

CMLT6427E

**ENHANCED SPECIFICATION  
SURFACE MOUNT, PICOmini™  
SILICON NPN DARLINGTON  
TRANSISTOR**

**ENHANCED  
SPECIFICATION**

**PICOmini™**



**SOT-563 CASE**

**Central™  
Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLT6427E is an Enhanced Specification, **PICOmini™**, NPN Silicon Darlington Transistor. High DC Current gains, coupled with a Low Saturation Voltage, make this an excellent choice for industrial/consumer applications where operational efficiency and small size are top priority.

**MARKING CODE : C64**

**FEATURES:**

- HIGH CURRENT (500mA MAX)
- HIGH DC CURRENT GAIN (15K MIN)
- LOW SATURATION VOLTAGE ( $V_{CE(SAT)} = 0.8V$  MAX)
- HIGH INPUT IMPEDANCE
- **PICOmini™** SOT-563 SURFACE MOUNT PACKAGE

**APPLICATIONS:**

- MOTOR DRIVERS
- RELAY DRIVERS
- PRE-AMPLIFIER INPUT APPLICATIONS
- VOLTAGE REGULATOR CONTROLS

**MAXIMUM RATINGS:** ( $T_A = 25^\circ C$ )

	SYMBOL		UNITS
◆ Collector-Base Voltage	$V_{CBO}$	60	V
◆ Collector-Emitter Voltage	$V_{CES}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	12	V
Continuous Collector Current	$I_C$	500	mA
Power Dissipation	$P_D$	350	mW (Note 1)
Power Dissipation	$P_D$	300	mW (Note 2)
Power Dissipation	$P_D$	150	mW (Note 3)
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ C$
Thermal Resistance	$\theta_{JA}$	357	$^\circ C/W$ (Note 1)

**ELECTRICAL CHARACTERISTICS:** ( $T_A = 25^\circ C$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CBO}$	$V_{CB} = 30V$			100	nA
◆ $I_{CEO}$	$V_{CE} = 25V$			100	nA
$I_{EBO}$	$V_{BE} = 10V$			100	nA
◆ $BV_{CBO}$	$I_C = 100\mu A$	60			V
◆ $BV_{CES}$	$I_C = 100\mu A$	60			V
$BV_{CEO}$	$I_C = 10mA$	40			V

◆ Enhanced Specification

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0 mm<sup>2</sup>  
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0 mm<sup>2</sup>  
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4 mm<sup>2</sup>

R0 (18-October 2005)

## ENHANCED SPECIFICATION

### SURFACE MOUNT, PICOmini<sup>TM</sup>

### SILICON NPN DARLINGTON

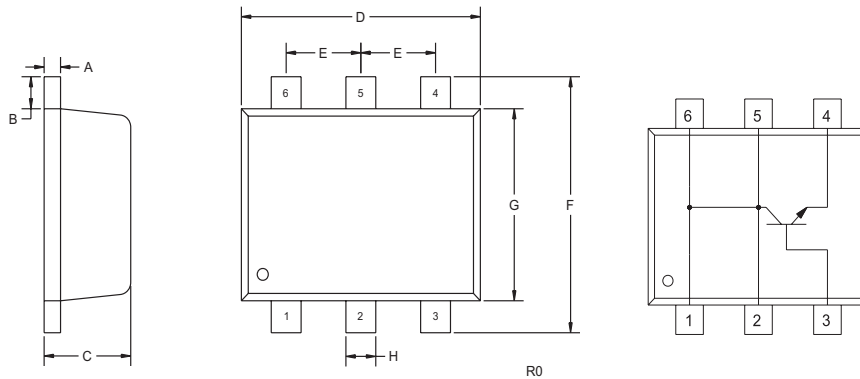
### TRANSISTOR

ELECTRICAL CHARACTERISTICS: ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
◆ $BV_{EBO}$	$I_E=10\mu\text{A}$	14			V
◆ $V_{CE(SAT)}$	$I_C=50\text{mA}$ , $I_B=0.5\text{mA}$			0.80	V
$V_{CE(SAT)}$	$I_C=100\text{mA}$ , $I_B=0.1\text{mA}$			0.85	V
◆ $V_{CE(SAT)}$	$I_C=500\text{mA}$ , $I_B=0.5\text{mA}$			1.0	V
$V_{BE(SAT)}$	$I_C=500\text{mA}$ , $I_B=0.5\text{mA}$			2.00	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}$ , $I_C=50\text{mA}$			1.75	V
◆ $h_{FE}$	$V_{CE}=5.0\text{V}$ , $I_C=10\text{mA}$	15K		100K	
◆ $h_{FE}$	$V_{CE}=5.0\text{V}$ , $I_C=100\text{mA}$	25K		200K	
◆ $h_{FE}$	$V_{CE}=5.0\text{V}$ , $I_C=500\text{mA}$	15K		140K	
$f_T$	$V_{CE}=5.0\text{V}$ , $I_C=10\text{mA}$ , $f=100\text{MHz}$		200		MHz
$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=1.0\text{MHz}$			7.0	pF
$C_{ib}$	$V_{BE}=0.5\text{V}$ , $I_C=0$ , $f=1.0\text{MHz}$			15	pF
NF	$V_{CE}=5.0\text{V}$ , $I_C=1.0\text{mA}$ , $R_S=100\text{k}\Omega$ , $f=1.0\text{kHz}$ TO $15.7\text{kHz}$			10	dB

◆ Enhanced Specification

### SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

#### LEAD CODE:

- 1) COLLECTOR
- 2) COLLECTOR
- 3) BASE
- 4) EMITTER
- 5) COLLECTOR
- 6) COLLECTOR

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R0 (18-October 2005)